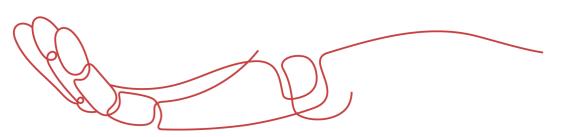


PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

ESD Protection Diode Array

Features

- 60Watts peak pulse power (tp = $8/20\mu s$)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.2pF typ. I/O to I/O)
- IEC 61000-4-2 ±20kV contact ±25kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20µs)

3 2

Applications

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3,eSATA
- Unified Display interface
- Digital Visual Interface
- High speed serial interface

Mechanical Data

- Tiny DFN2510(2.5mmx1.0mm) package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant



Absolute Maximum Rating

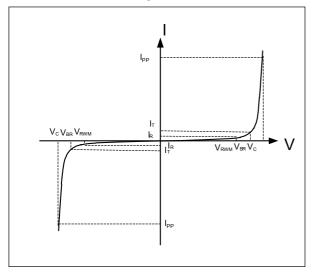
Rating	Symbol	Value	Units	
Peak Pulse Power (t _p =8/20μs)	P _{PP}	60	Watts	
Peak Pulse Current (t _p =8/20μs) (note1)	I_{PP}	4	А	
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	25 20	kV	
Lead Soldering Temperature	T_L	260(10seconds)	$^{\circ}\!\mathbb{C}$	
Junction Temperature	T _J	-55 to + 125	$^{\circ}\!\mathbb{C}$	
Storage Temperature	T_{stg}	-55 to + 125	$^{\circ}\!\mathrm{C}$	

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	6.0			V
Reverse Leakage Current	I _R	V _{RWM} =5V,T=25℃			1	μΑ
Peak Pulse Current	l _{PP}	tp =8/20μs			4	Α
Clamping Voltage	V _C	I _{PP} =4A,t _p =8/20μs			15	V
Junction Capacitance	C _j	V _R = 0V, f = 1MHz I/O to I/O		0.2	0.35	pF
		V _R = 0V, f = 1MHz I/O to GND		0.4	0.55	рΓ

Electrical Parameters (TA = 25°C unless otherwise noted)

	Parameter		
I _{PP}	MaximumReversePeak Pulse Current		
V _C	Clamping Voltage @ I _{PP}		
V_{RWM}	WorkingPeak Reverse Voltage		
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
V_{BR}	Breakdown Voltage @ I _T		
I _T	Test Current		



Note:.8/20µs pulse waveform.



Typical Characteristic Curves

Fig.1 Peak Pulse Power Rating Curve

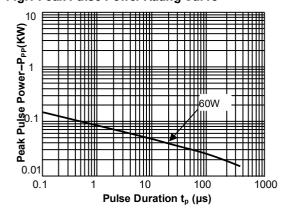


Fig.3 Pulse Waveform-8/20µs

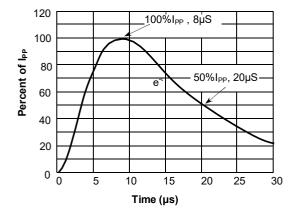


Fig.2 Pulse Derating Curve

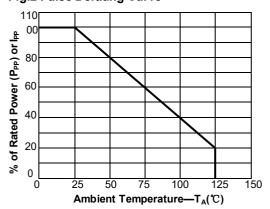
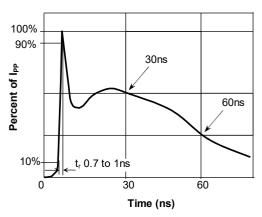
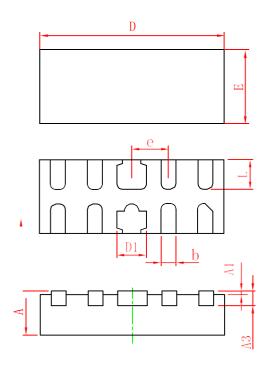


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





Outline Drawing - DFN2510(2.5mmx1.0mm)



Symbol	Dimensions in millimeters				
Symbol	Min	Nom	Max		
Α	0.45	0.50	0.55		
A1	-	0.02	0.05		
A3	0.10	0.15	0.20		
D	2.45	2.50	2.55		
E	0.95	1.00	1.05		
D1	0.35	0.40	0.45		
b	0.15	0.20	0.25		
е	0.50BSC				
L	0.35	0.40	0.45		



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